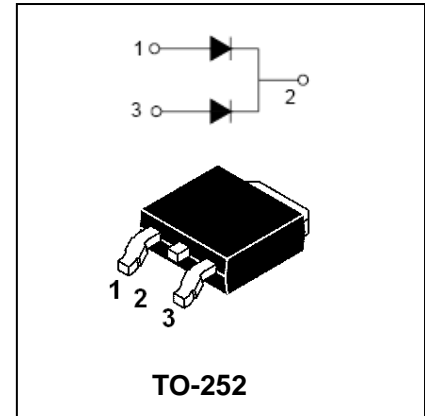


FEATURES

- * Glass passivated chip
- * Superfast switching time for high efficiency
- * Low forward voltage drop and high current capability
- * Low reverse leakage current
- * High surge capacity

Applications:

- * Switching Power Supply
- * Power Switching Circuits
- * General Purpose



Rating	Symbol	MURD620	Unit
Maximum Repetitive Reverse Voltage	VRRM	200	V
DC Blocking Voltage	VDC	200	V
Maximum Average Forward Current	I _{AV}	6.0	A
Peak Forward Surge Current ,8.3ms single half sine-wave superimposed on rated load(JEDEC method)	I _{FSM}	80.0	A
Maximum Forward Voltage at 6A,per element	V _F	1.20	V
Maximum DC Reverse Current at T _A =25°C	I _R	5.0	μA
Rated DC Blocking Voltage T _A =100°C		500.0	
Maximum Reverse Recovery Time (Note 1)	T _{RR}	35	ns
Maximum Thermal Resistance(Note 2)	R _{θ-JA}	3.5	°C/W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to +150	°C

NOTES:

1. Reverse Recovery Test Conditions: I_F=.5A, I_R=1A, I_{rr}=.25A.
2. Thermal resistance from junction to ambient

■ Typical Characteristics

FIG.1 - FORWARD CURRENT DERATING CURVE

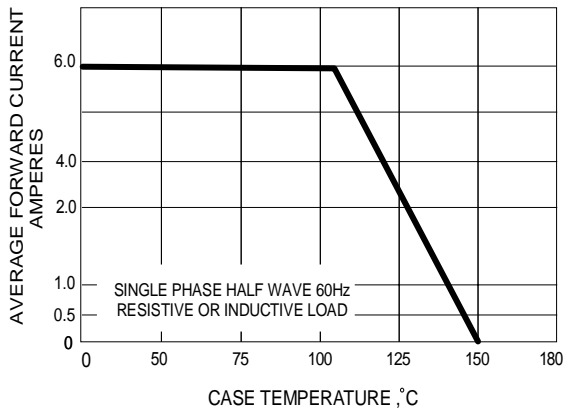


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

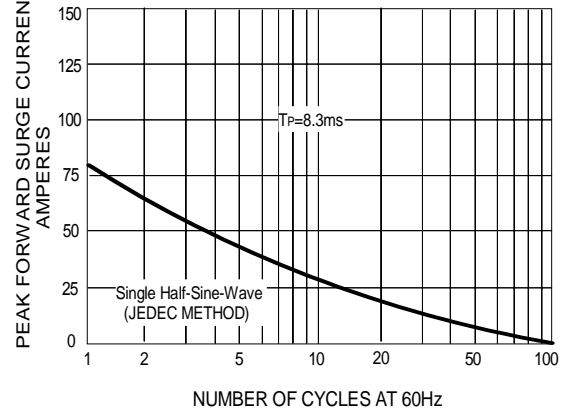


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

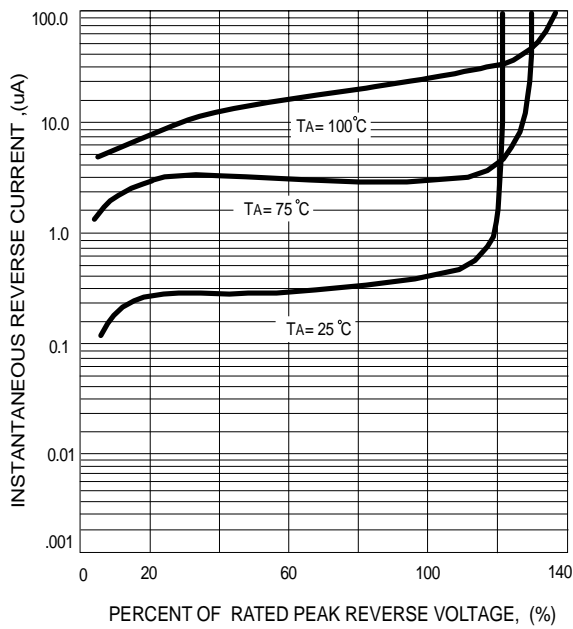
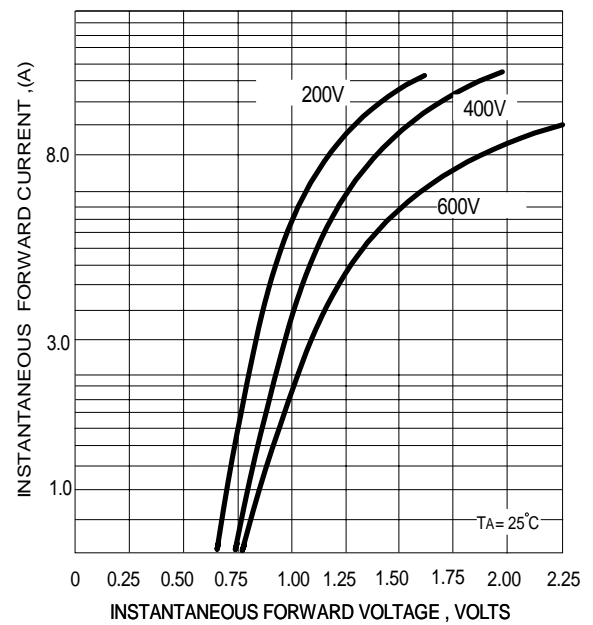


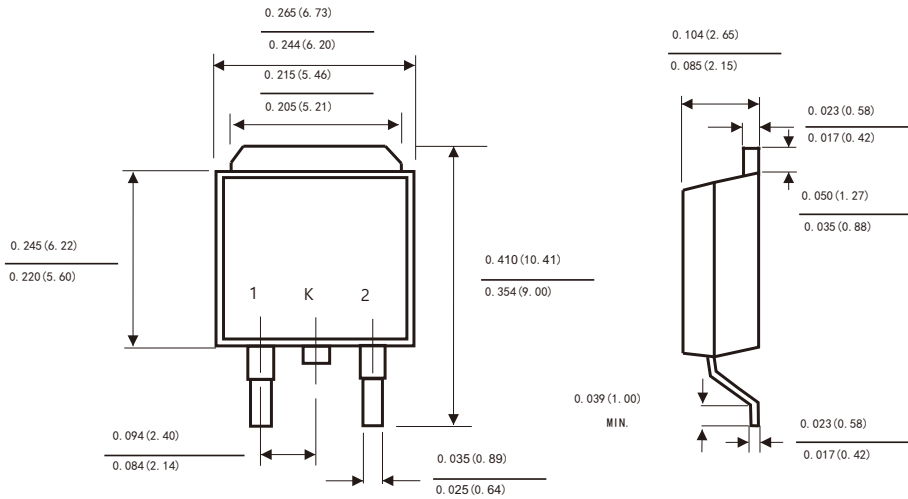
FIG.4 - TYPICAL FORWARD CHARACTERISTICS



Package Outline Dimensions

Dimensions in inches and (millimeters)

TO-252



Suggested Pad Layout

